

Schottky Diode

$$V_{RRM} = 100\text{ V}$$

$$I_{FAV} = 2 \times 60\text{ A}$$

$$V_F = 0.74\text{ V}$$

High Performance Schottky Diode
 Low Loss and Soft Recovery
 Parallel legs

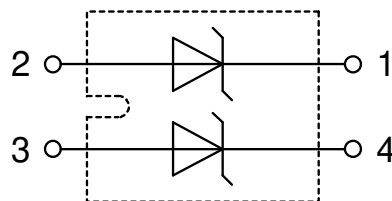
Part number

DSS2x61-01A



Backside: isolated

 E72873



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					100	V
V_{RRM}	max. repetitive reverse blocking voltage					100	V
I_R	reverse current, drain current	$V_R = 100\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		2	mA
		$V_R = 100\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		20	mA
V_F	forward voltage drop	$I_F = 60\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.91	V
		$I_F = 120\text{ A}$				1.10	V
		$I_F = 60\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.74	V
		$I_F = 120\text{ A}$				0.95	V
I_{FAV}	average forward current	$T_C = 105^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		60	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.49	V
r_F	slope resistance					3.5	mΩ
R_{thJC}	thermal resistance junction to case					0.8	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		150	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		700	A
C_J	junction capacitance	$V_R = 12\text{ V}$	$f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		863	pF



Package SOT-227B (minibloc)		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8		mm
V_{ISOL}	isolation voltage	t = 1 second		3000		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS2x61-01A	DSS2x61-01A	Tube	10	470961

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Schottky

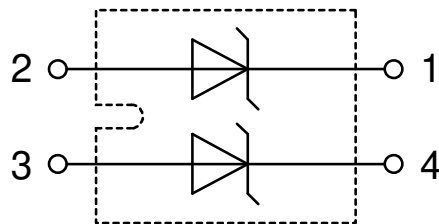
$V_{0\ max}$	threshold voltage	0.49	V
$R_{0\ max}$	slope resistance *	1.7	mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



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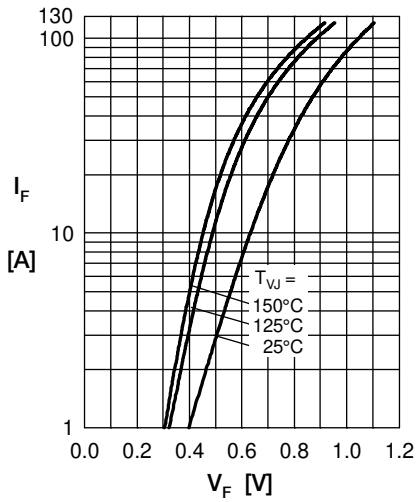


Fig. 1 Maximum forward voltage drop characteristics

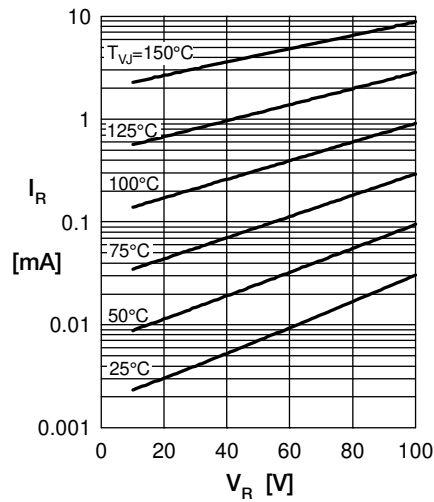


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

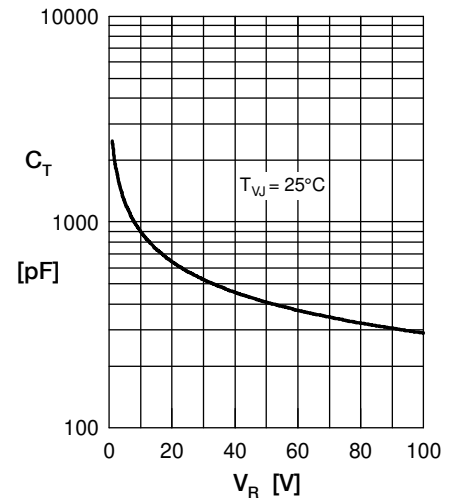


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

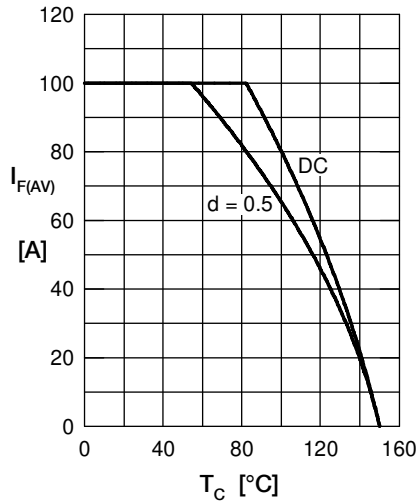


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C

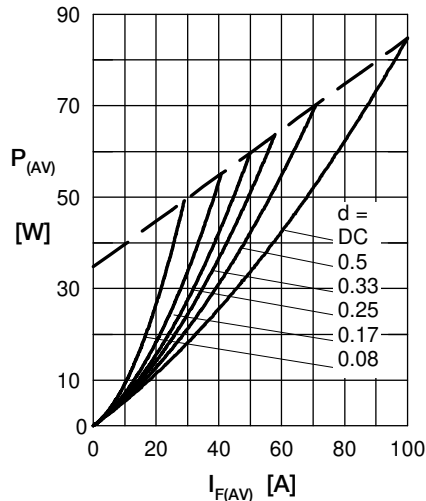


Fig. 5 Forward power loss characteristics

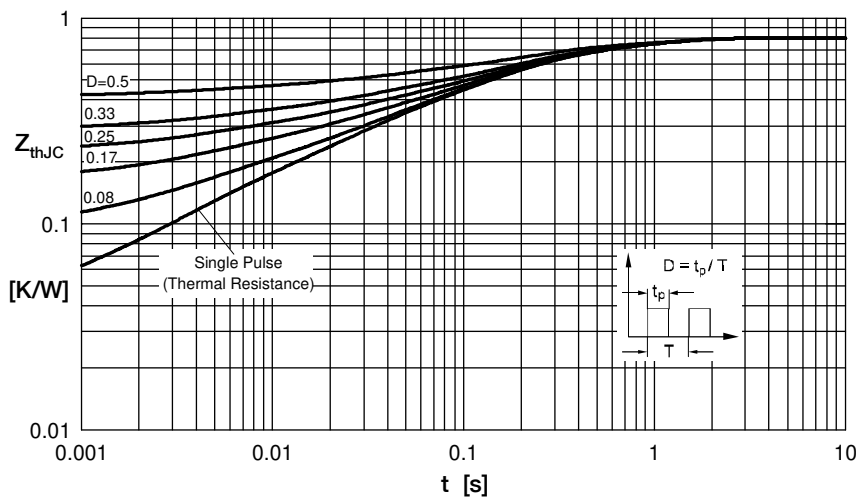


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode